

Chemical Vapor Transport Synthesis of One-Dimensional V_2PS_{10} and Its Application in Miniaturized UV Sensors

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SUPPORTING FIGURES

Morphology of V_2PS_{10} nanowire synthesized by various reaction condition

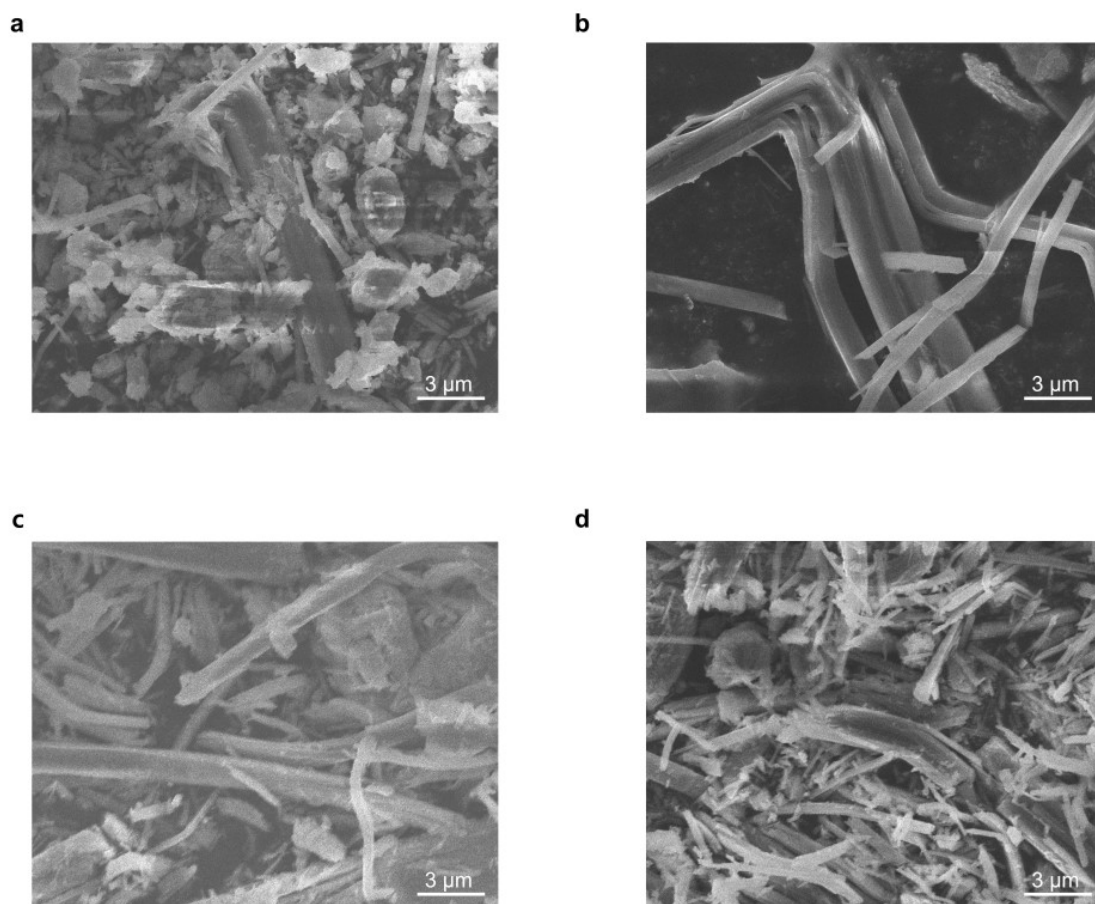


Fig. S1 SEM image of V_2PS_{10} nanowire synthesized by various reaction condition. (a) Using VS_4 as intermediate phase precursor instead of Vanadium precursor and heated to $450^\circ C$ for 3 days. (b), (c), and (d) Using V, P and S as precursor. (b) $500^\circ C$ for 3 days. (c) $480^\circ C$ for 7 days. (d) $500^\circ C$ for 7 days.

The expanded XRD peaks of V_2PS_{10} powder under various synthesis conditions

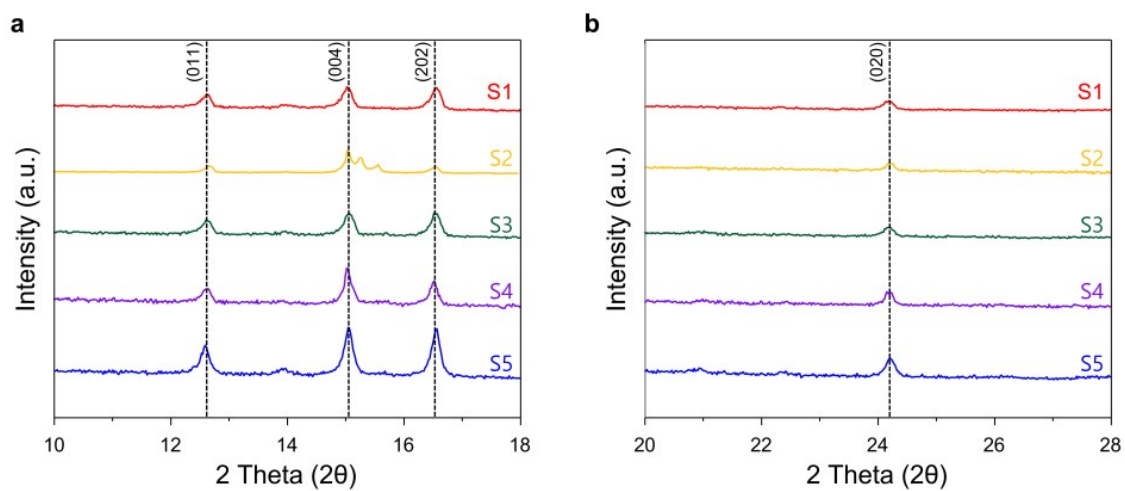
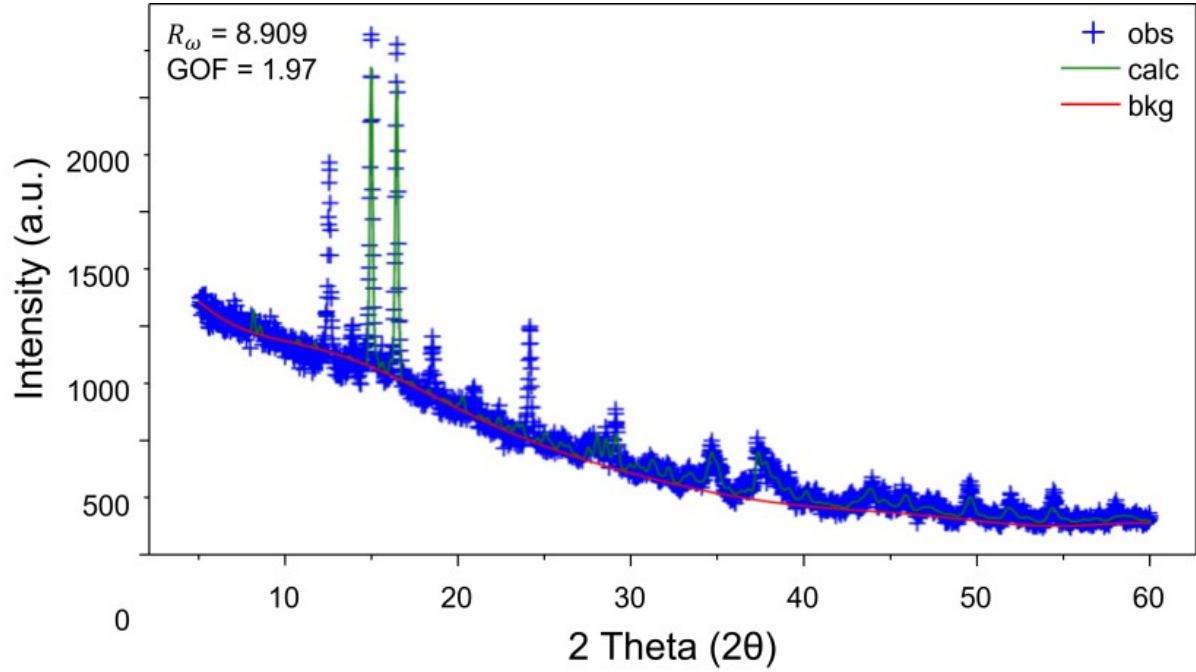


Fig. S2 The expanded XRD peaks in Figure 2b. (a) $10^\circ < 2\theta < 18^\circ$. (b) $20^\circ < 2\theta < 28^\circ$.

The result of Rietveld refinement of the XRD graph of the V_2PS_{10} powder by CVT method



$$\otimes R_{\omega} = \sqrt{\frac{\sum_i \omega_i (y_{obs,i} - y_{calc,i})^2}{\sum_i \omega_i y_{obs,i}^2}},$$

R_{ω} = weighted residual factor

$$\otimes GOF = \frac{R_{\omega}}{R_{expected}} = \sqrt{\frac{\sum_i \omega_i (y_{obs,i} - y_{calc,i})^2}{N - P}},$$

$R_{expected}$ = The expected R value, which represents the ideal level of data fit.
 N = The total number of data points.
 P = The number of refined parameters.

Fig. S3 The results of Rietveld refinement of the XRD graph under S5 condition.

Morphology and atomic ratio of the V_2PS_{10} nanowires synthesized by CVT method

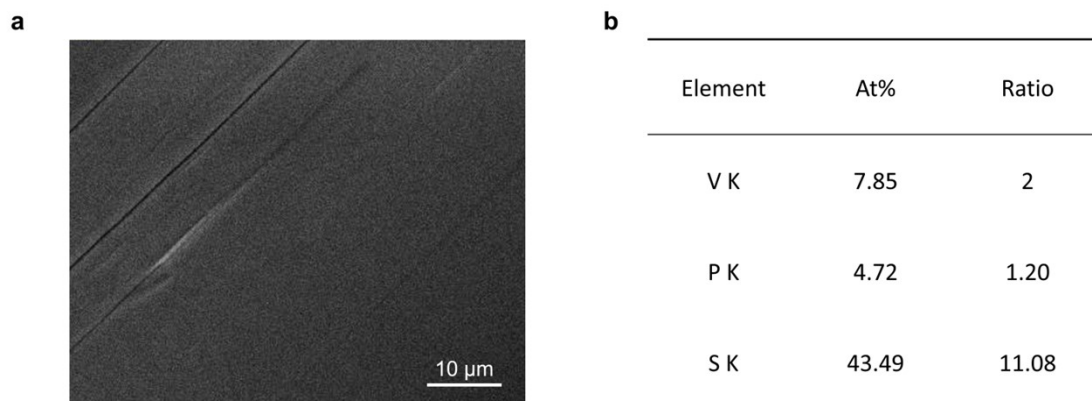


Fig. S4 (a) SEM image of the V_2PS_{10} single crystal nanowire synthesized by CVT method. (b) The ratio of the elements obtained by EDS.

Dispersion of the V₂PS₁₀ nanowires with various solvent













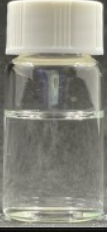







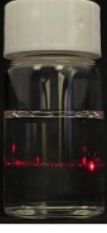



Material	V ₂ PS ₁₀							
Sonication	3hr							
RPM	6000							
Solvent	Toluen e	Chlorof orm	Aceton e	IPA	Ethanol	DMF	NMP	DI
After Sonication								
After Centrifugation								
Tyndall Effect								

Fig. S5 Tyndall effect of V₂PS₁₀ solutions dispersed in various solvents.

Absorbance graph according to dielectric constant and surface tension of various solvents

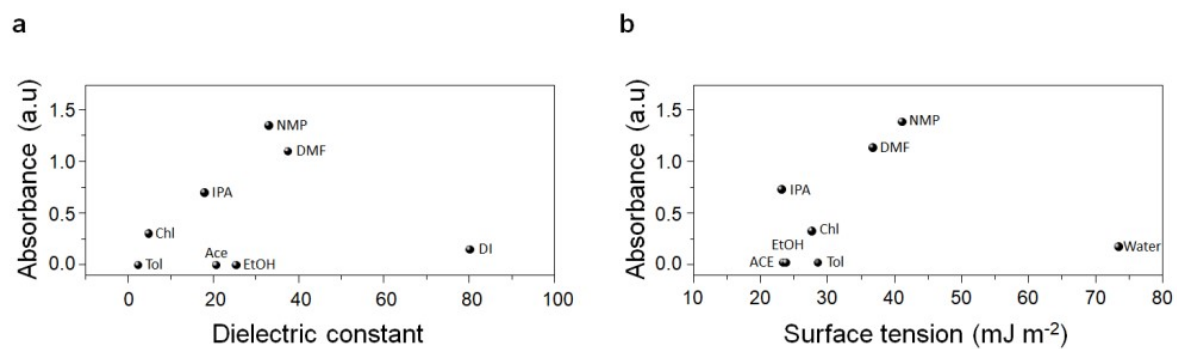


Fig. S6 (a) Dielectric constant vs Absorbance graph of dispersed solvent. (b) Surface tension vs Absorbance graph of dispersed solvent.

Comparison of rise/decay time and on/off ratio of various 1D material-based UV sensors

material	year	rise time (ms)	decay time (ms)	on/off ratio	Ref.
ZnS nanowire	2017	90	70	19173	1
WO ₃	2023	75	69	-	2
CsCu ₂ I ₃	2021	160	320	3150	3
ZnO nanowire	2017	450	60	100	4
TiO ₂ nanowire	2018	400	100	2000	5
V ₂ PS ₁₀	2024	60.1	214.4	16395	This work

Table. S1 Comparison of rise/decay time and on/off ratio of various 1D material-based UV sensors

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